Unit: mm

TOSHIBA Field Effect Transistor Silicon N Channel MOS Type ( $\pi$ -MOSVII)

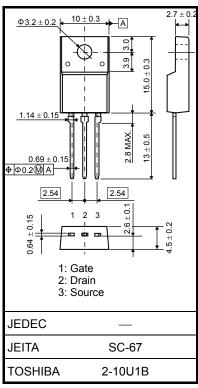
# TK6A53D

## **Switching Regulator Applications**

- Low drain-source ON-resistance: RDS (ON) =  $1.1 \Omega$  (typ.)
- High forward transfer admittance:  $|Y_{fs}| = 2.5 \text{ S (typ.)}$
- Low leakage current:  $I_{DSS} = 10 \mu A \text{ (max) (V}_{DS} = 525 \text{ V)}$
- Enhancement mode:  $V_{th} = 2.4 \text{ to } 4.4 \text{ V (V}_{DS} = 10 \text{ V, I}_{D} = 1 \text{ mA)}$

### **Absolute Maximum Ratings (Ta = 25°C)**

| Characteristics                        |                              | Symbol           | Rating     | Unit |  |
|--|------------------------------|------------------|------------|------|--|
| Drain-source voltage                   |                              | $V_{DSS}$        | 525        | V    |  |
| Gate-source voltage                    |                              | V <sub>GSS</sub> | ±30        | V    |  |
| Drain current                          | DC (Note 1)                  | I <sub>D</sub>   | 6          |      |  |
|  | Pulse (t = 1 ms)<br>(Note 1) | I <sub>DP</sub>  | 24         | Α    |  |
| Drain power dissipati                  | on (Tc = 25°C)               | P <sub>D</sub>   | 35         | W    |  |
| Single pulse avalanche energy (Note 2) |                              | E <sub>AS</sub>  | 147        | mJ   |  |
| Avalanche current                      |                              | I <sub>AR</sub>  | 6          | Α    |  |
| Repetitive avalanche energy (Note 3)   |                              | E <sub>AR</sub>  | 3.5        | mJ   |  |
| Channel temperature                    |                              | T <sub>ch</sub>  | 150        | °C   |  |
| Storage temperature range              |                              | T <sub>stg</sub> | -55 to 150 | °C   |  |

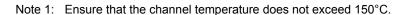


Weight: 1.7 g (typ.)

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

#### **Thermal Characteristics**

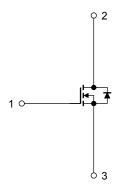
| Characteristics                        | Symbol                 | Max  | Unit |
|--|------------------------|------|------|
| Thermal resistance, channel to case    | R <sub>th (ch-c)</sub> | 3.57 | °C/W |
| Thermal resistance, channel to ambient | R <sub>th (ch-a)</sub> | 62.5 | °C/W |



Note 2:  $V_{DD} = 90 \text{ V}$ ,  $T_{ch} = 25^{\circ}\text{C}(\text{initial})$ , L = 7.02 mH,  $R_G = 25 \Omega$ ,  $I_{AR} = 6 \text{ A}$ 

Note 3: Repetitive rating: pulse width limited by maximum channel temperature

This transistor is an electrostatic-sensitive device. Handle with care.



Start of commercial production 2009-02

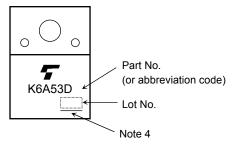
# **Electrical Characteristics (Ta = 25°C)**

| Chara                          | acteristics   | Symbol               | Test Condition  | Min | Тур. | Max | Unit |
|--------------------------------|---------------|----------------------|---|-----|------|-----|------|
| Gate leakage current           |               | I <sub>GSS</sub>     | $V_{GS} = \pm 30 \text{ V}, V_{DS} = 0 \text{ V}$   | _   | _    | ±1  | μΑ   |
| Drain cut-off current          |               | I <sub>DSS</sub>     | V <sub>DS</sub> = 525 V, V <sub>GS</sub> = 0 V  | _   | _    | 10  | μΑ   |
| Drain-source breakdown voltage |               | V (BR) DSS           | I <sub>D</sub> = 10 mA, V <sub>GS</sub> = 0 V   | 525 | _    | _   | V    |
| Gate threshold vo              | oltage        | V <sub>th</sub>      | V <sub>DS</sub> = 10 V, I <sub>D</sub> = 1 mA   | 2.4 | _    | 4.4 | V    |
| Drain-source ON                | -resistance   | R <sub>DS</sub> (ON) | V <sub>GS</sub> = 10 V, I <sub>D</sub> = 3 A  | _   | 1.1  | 1.3 | Ω    |
| Forward transfer               | admittance    | Y <sub>fs</sub>      | V <sub>DS</sub> = 10 V, I <sub>D</sub> = 3 A  | 0.7 | 2.5  | _   | S    |
| Input capacitance              |               | C <sub>iss</sub>     |   | _   | 600  | _   | pF   |
| Reverse transfer capacitance   |               | C <sub>rss</sub>     | V <sub>DS</sub> = 25 V, V <sub>GS</sub> = 0 V, f = 1 MHz  | _   | 4    | _   |      |
| Output capacitance             |               | C <sub>oss</sub>     |   |     | 70   | _   |      |
| Switching time                 | Rise time     | t <sub>r</sub>       | $\begin{array}{c c} 10 \text{ V} & \text{I}_D = 3 \text{ A} & \text{V}_{\text{OUT}} \\ \hline 0 \text{ V} & \text{SO} & \text{SO} & \text{SO} \\ \hline 50 \Omega & \text{V}_{\text{DD}} \approx 200 \text{ V} \end{array}$ | _   | 18   | _   | - ns |
|                                | Turn-on time  | t <sub>on</sub>      |   | _   | 40   | _   |      |
|                                | Fall time     | t <sub>f</sub>       |   | _   | 8    | _   |      |
|                                | Turn-off time | t <sub>off</sub>     | V <sub>DD</sub> ≈ 200 V<br>Duty ≤ 1%, t <sub>W</sub> = 10 μs  | _   | 55   | _   |      |
| Total gate charge              |               | Qg                   |   | _   | 12   | _   |      |
| Gate-source charge             |               | Q <sub>gs</sub>      | $V_{DD} \approx 400 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 6 \text{ A}$  | _   | 7    | _   | nC   |
| Gate-drain charge              |               | Q <sub>gd</sub>      |   | _   | 5    | _   |      |

# Source-Drain Ratings and Characteristics (Ta = 25°C)

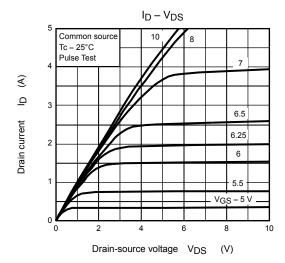
| Characteristics                           | Symbol           | Test Condition                                | Min | Тур. | Max  | Unit |
|---|------------------|---|-----|------|------|------|
| Continuous drain reverse current (Note 1) | I <sub>DR</sub>  | _   | _   | _    | 6    | Α    |
| Pulse drain reverse current (Note 1)      | I <sub>DRP</sub> | _   | _   | _    | 24   | Α    |
| Forward voltage (diode)                   | V <sub>DSF</sub> | I <sub>DR</sub> = 6 A, V <sub>GS</sub> = 0 V  | _   | _    | -1.7 | V    |
| Reverse recovery time                     | t <sub>rr</sub>  | I <sub>DR</sub> = 6 A, V <sub>GS</sub> = 0 V, | _   | 1200 | _    | ns   |
| Reverse recovery charge                   | Q <sub>rr</sub>  | dI <sub>DR</sub> /dt = 100 A/μs               | _   | 7    | _    | μС   |

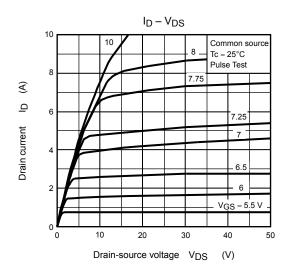
## Marking

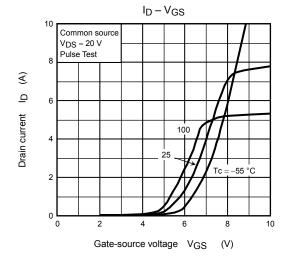


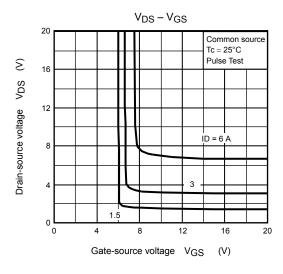
Note 4: A line under a Lot No. identifies the indication of product Labels [[G]]/RoHS COMPATIBLE or [[G]]/RoHS [[Pb]]

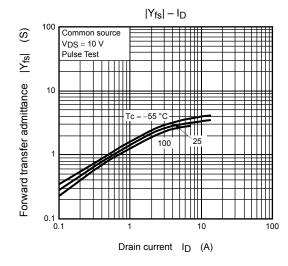
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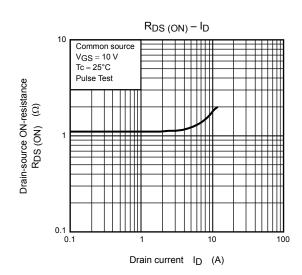


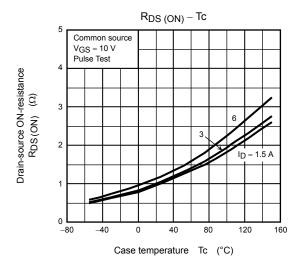


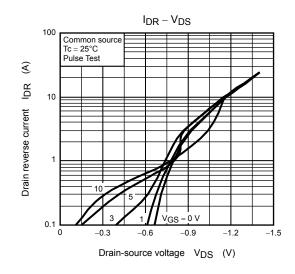


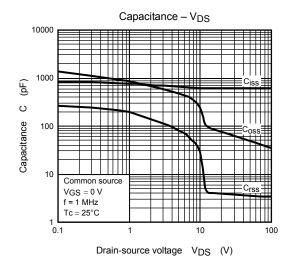


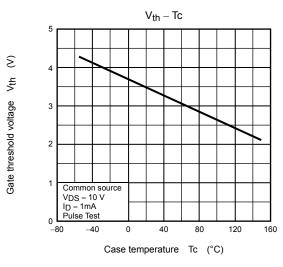


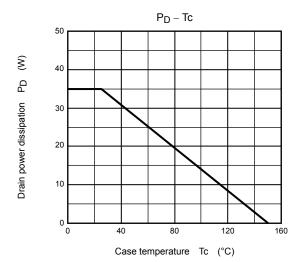


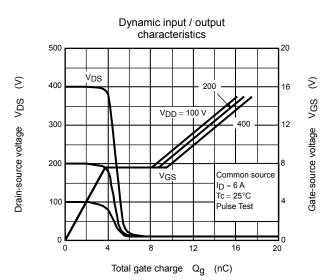


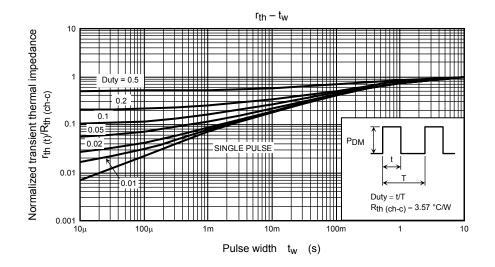


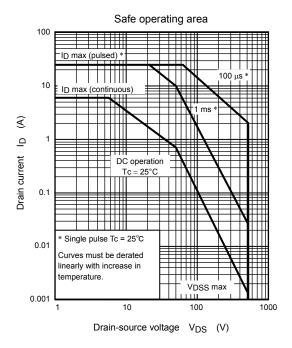


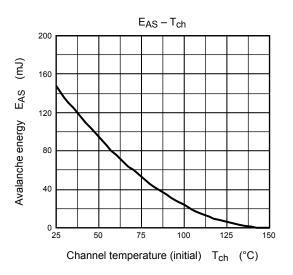


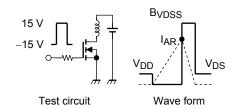












$$\begin{aligned} &R_G = 25~\Omega \\ &V_{DD} = 90~V,~L = 7.02~mH \end{aligned}$$

$$E_{AS} = \frac{1}{2} \cdot L \cdot I^2 \cdot \left( \frac{B_{VDSS}}{B_{VDSS} - V_{DD}} \right)$$

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